

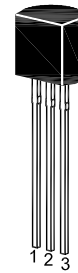
# ST 2SC2120

## NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into two groups, O and Y according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



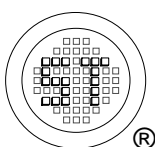
1. Emitter 2. Collector 3. Base  
TO-92 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	35	V
Collector Emitter Voltage	$V_{CEO}$	30	V
Emitter Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	800	mA
Base Current	$I_B$	160	mA
Power Dissipation	$P_{tot}$	600	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

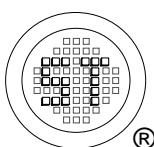
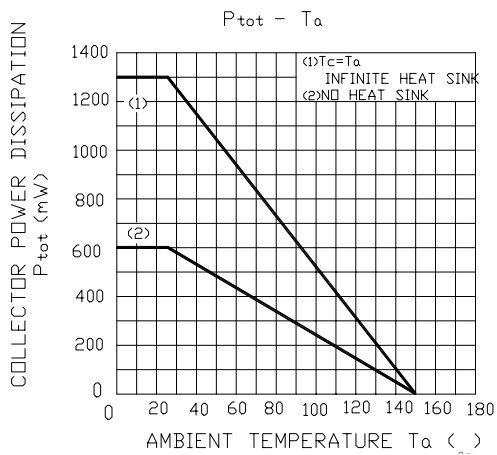
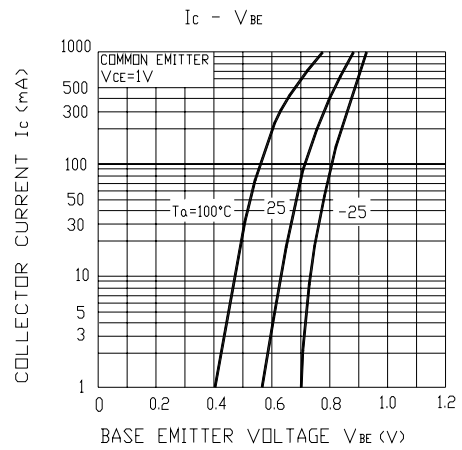
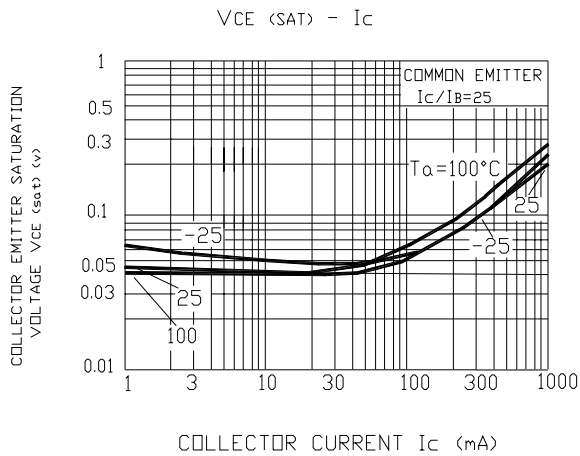
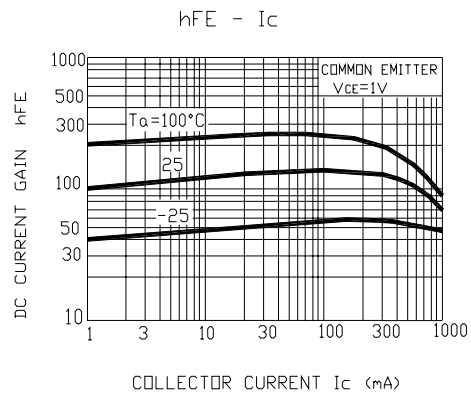
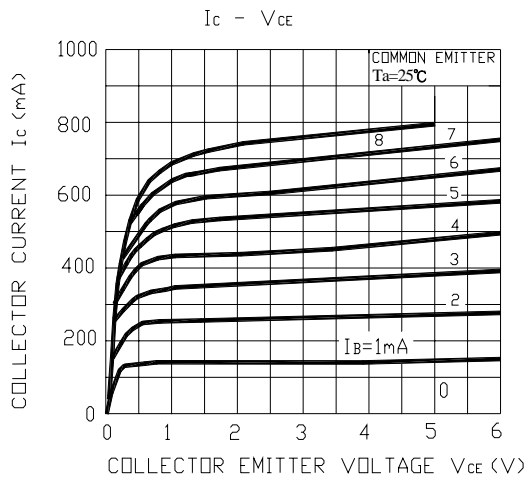
Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 1\text{ V}$ , $I_C = 100\text{ mA}$ Current Gain Group O Y	$h_{FE}$	100	-	200	-
	$h_{FE}$	160	-	320	-
	$h_{FE}$	35	-	-	-
at $V_{CE} = 1\text{ V}$ , $I_C = 700\text{ mA}$					
Collector Base Cutoff Current at $V_{CB} = 35\text{ V}$	$I_{CBO}$	-	-	0.1	$\mu\text{A}$
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	$I_{EBO}$	-	-	0.1	$\mu\text{A}$
Collector Emitter Breakdown Voltage at $I_C = 10\text{ mA}$	$V_{CEO}$	30	-	-	V
Collector Emitter Saturation Voltage at $I_C = 500\text{ mA}$ , $I_B = 20\text{ mA}$	$V_{CE(sat)}$	-	-	0.5	V
Base Emitter Voltage at $I_C = 10\text{ mA}$ , $V_{CE} = 1\text{ V}$	$V_{BE}$	0.5	-	0.8	V
Transition Frequency at $V_{CE} = 5\text{ V}$ , $I_C = 10\text{ mA}$	$f_T$	-	120	-	MHz
Collector Output Capacitance at $V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$	$C_{ob}$	-	13	-	pF



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Dated : 07/12/2002



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